

L Number	Hits	Search Text	DB	Time stamp
1	149	((("TiN") or (titanium adj nitride)) and (CF4 or tetrafluoromethane) and (O2 or oxygen)	USPAT	2002/05/16 18:25
2	149	((("TiN") or (titanium adj nitride)) and (CF4 or tetrafluoromethane) and (O2 or oxygen)) and (etch\$3 or pattern\$3 or defin\$3 or form\$3)	USPAT	2002/05/16 18:07
3	140	((("TiN") or (titanium adj nitride)) and (CF4 or tetrafluoromethane) and (O2 or oxygen)) and (etch\$3 or pattern\$3 or defin\$3)	USPAT	2002/05/16 18:08
4	235	((("TiN") or (titanium adj nitride) or barrier or etch\$1stop) and (CF4 or tetrafluoromethane) and (O2 or oxygen)	USPAT	2002/05/16 18:08
5	219	((("TiN") or (titanium adj nitride) or barrier or etch\$1stop) and (CF4 or tetrafluoromethane) and (O2 or oxygen)) and (etch\$3 or pattern\$3 or defin\$3)	USPAT	2002/05/16 18:08
6	45	(titanium adj nitride) and (CF4 or tetrafluoromethane) and (O2 or oxygen)	USPAT	2002/05/16 18:25
7	1568	(titanium adj nitride) and (silicon adj carbide)	USPAT	2002/05/16 18:20
8	126	((titanium adj nitride) and (silicon adj carbide)) and (barrier adj layer)	USPAT	2002/05/16 18:21
9	9	((titanium adj nitride) and (silicon adj carbide)) and (etch\$1stop adj layer)	USPAT	2002/05/16 18:24
10	51	(SiC or (Silicon adj carbide)) and (CF4 or tetrafluoromethane) and (O2 or oxygen)	USPAT	2002/05/16 18:27
11	570	((SiC or (Silicon adj carbide))near\$4 etch\$3) and (CF4 or tetrafluoromethane) and (O2 or oxygen)	USPAT	2002/05/16 18:28
12	313	((SiC or (Silicon adj carbide))near\$4 etch\$3) and (CF4 or tetrafluoromethane) and (O2 or oxygen) and (ar or argon)	USPAT	2002/05/16 18:30
13	916094	((SiC or (Silicon adj carbide))near\$4 etch\$3)	USPAT	2002/05/16 18:32
14	313	((SiC or (Silicon adj carbide))near\$4 etch\$3) ) and (CF4 or tetrafluoromethane) and (O2 or oxygen) and (ar or argon)	USPAT	2002/05/16 18:34
15	37675	(SiC or (Silicon adj carbide))	USPAT	2002/05/16 18:42
16	916094	((SiC or (Silicon adj carbide))) near\$4 etch\$3	USPAT	2002/05/16 18:34
17	883749	((SiC or (Silicon adj carbide))) near\$2 etch\$3	USPAT	2002/05/16 18:34
18	312	((SiC or (Silicon adj carbide))) near\$2 etch\$3) and (CF4 or tetrafluoromethane) and (O2 or oxygen) and (ar or argon)	USPAT	2002/05/16 18:41
19	239	((SiC or (Silicon adj carbide))) near\$2 etch\$3) and (CF4 or tetrafluoromethane) and (O2 or oxygen) and (ar or argon)) and substrate	USPAT	2002/05/16 18:36
20	27	((SiC or (Silicon adj carbide))) near\$2 etch\$3) and (CF4 or tetrafluoromethane) and (O2 or oxygen) and (ar or argon)) and substrate) and (SiC or (Silicon adj carbide))	USPAT	2002/05/16 18:37
21	108	((SiC or (Silicon adj carbide))) near\$2 etch\$3) and (CH2f2 or difluoromethane) and (O2 or oxygen) and (ar or argon)	USPAT	2002/05/16 19:00
22	53	((SiC or (Silicon adj carbide))) near\$2 etch\$3) and (CH2f2 or difluoromethane) and (O2 or oxygen) and (ar or argon)) and substrate	USPAT	2002/05/16 18:42
23	12	((SiC or (Silicon adj carbide))) near\$2 etch\$3) and (CH2f2 or difluoromethane) and (O2 or oxygen) and (ar or argon)) and substrate) and (SiC or (Silicon adj carbide))	USPAT	2002/05/16 18:45
24	37675	(SiC or (Silicon adj carbide))	USPAT	2002/05/16 18:45

25	14	((SiC or (Silicon adj carbide))) and (CH2f2 or difluoromethane) and (O2 or oxygen) and (ar or argon)	USPAT	2002/05/16 18:49
26	195	(CH2f2 or difluoromethane) and (O2 or oxygen) and (ar or argon) and (n2 or nitrogen)	USPAT	2002/05/16 18:50
27	37	((CH2f2 or difluoromethane) and (O2 or oxygen) and (ar or argon) and (n2 or nitrogen) ) and strip\$4	USPAT	2002/05/16 18:51
28	10	((CH2f2 or difluoromethane) and (O2 or oxygen) and (ar or argon) and (n2 or nitrogen) ) and strip\$4) and (resist or photo\$1resist or photo\$polymer)	USPAT	2002/05/16 18:59
29	44499	(resist or photo\$1resist or photo\$polymer) and strip\$4	USPAT	2002/05/16 19:00
30	1142619	(resist or photo\$1resist or photo\$polymer) near\$2 strip\$4	USPAT	2002/05/16 19:01
31	123	((resist or photo\$1resist or photo\$polymer) near\$2 strip\$4 ) and (CH2f2 or difluoromethane) and (O2 or oxygen) and (ar or argon)	USPAT	2002/05/16 19:02
32	8066	(resist or photo\$1resist or photo\$polymer) near2 strip\$4	USPAT	2002/05/16 19:01
33	8	((resist or photo\$1resist or photo\$polymer) near2 strip\$4 ) and (CH2f2 or difluoromethane) and (O2 or oxygen) and (ar or argon)	USPAT	2002/05/16 19:05
34	5	((resist or photo\$1resist or photo\$polymer) near2 strip\$4 ) and (CH2f2 or difluoromethane) and (O2 or oxygen) and (ar or argon) and (n2 or nitrogen)	USPAT	2002/05/16 19:06